



#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
60V	$3\Omega$ @ $V_{GS} = 10V$	300mA

#### **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

#### **Applications**

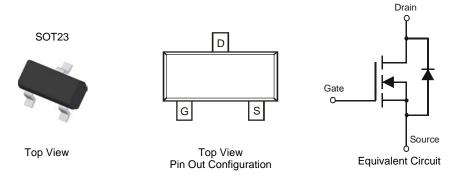
- Motor Control
- **Power Management Functions**

#### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (approximate)



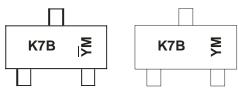
## **Ordering Information** (Note 4)

Part Number	Case	Packaging
2N7002E-7-F	SOT23	3,000/Tape & Reel
2N7002E-13-F	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



Chengdu A/T Site

Shanghai A/T Site

K7B = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or  $\overline{Y}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

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Date Code K	ey														
Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	Р	R	S	T	U	V	W	Χ	Υ	Z	Α	В	C	D	Е
					•					•					•
Month	Jan	Fe	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t l	VoV	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	60	V	
Drain-Gate Voltage R <sub>GS</sub> ≤ 1.0MΩ		$V_{DGR}$	60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20 ±40	V		
Continuous Drain Current (Note 5) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	250 200	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	300 240	mA		
Maximum Body Diode Forward Current (Note 6)		Is	500	mA	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	1	I <sub>DM</sub>	800	mA	

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D-	370	mW	
Total Fower Dissipation	(Note 6)	P <sub>D</sub>	540		
Thermal Resistance, Junction to Ambient	(Note 5)	В	348		
memai Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	$R_{\theta JC}$	91			
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	

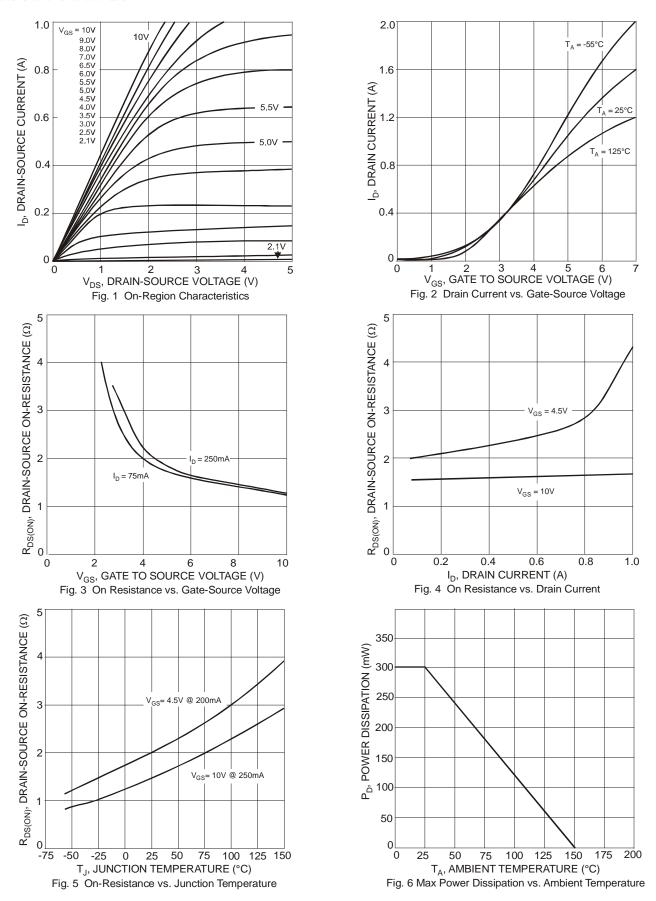
# **Electrical Characteristics** (@ $T_A = \pm 25$ °C, unless otherwise specified.)

Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	60	70		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25^{\circ}C$ @ $T_C = +125^{\circ}C$			_		1.0 500	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage		I <sub>GSS</sub>	_	_	±10	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V <sub>GS(th)</sub>	1.0	_	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
Static Drain-Source On-Resistance	@ T <sub>J</sub> = +25°C	R <sub>DS</sub> (ON)		1.6 2.0	3 4	Ω	$V_{GS} = 10V, I_D = 250mA$ $V_{GS} = 4.5V, I_D = 200mA$
On-State Drain Current		I <sub>D(ON)</sub>	8.0	1.0	_	Α	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance			80	_	—	mS	V <sub>DS</sub> =10V, I <sub>D</sub> = 0.2A
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance			_	22	50	pF	
Output Capacitance		Coss		11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C <sub>rss</sub>	_	2.0	5.0	pF	
Gate resistance		Rg		120	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)			_	223		рC	
Gate-Source Charge		Q <sub>gs</sub>	_	82		рC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Drain Charge			_	178		рC	
SWITCHING CHARACTERISTICS (Note	8)						
Turn-On Delay Time			_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t <sub>D(OFF)</sub>	_	11	20	ns	$R_L = 150\Omega$ , $V_{GEN} = 10V$ , $R_{GEN} = 25\Omega$

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

<sup>6.</sup> Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

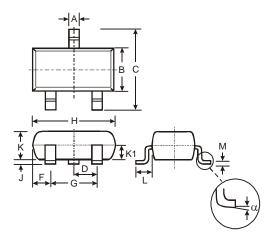






# **Package Outline Dimensions**

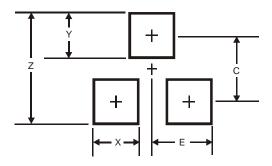
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
Н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
K	0.903	1.10	1.00						
K1	-	-	0.400						
L	0.45	0.61	0.55						
M	0.085	0.18	0.11						
α	0°	8°	-						
All	All Dimensions in mm								

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
Е	1.35

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